Effect of background impurities and electronic excitation on the behavior of radiation induced interstitial boron complexes

Wednesday 11 June 2014 09:30 (20 minutes)

New experimental data have been presented on substitutional boron removal under irradiation and its restoration under thermal and recombination annealing in epitaxial Si structures.

Author: MAKARENKO, Leonid (B)

Co-authors: Dr PINTILIE, Ioana (NIMP Bucharest-Magurele, Romania); MOLL, Michael (CERN); Dr LAS-TOVSKII, Stanislav (Scientific-Practical Materials Research Centre of NAS of Belarus)

Presenter: MAKARENKO, Leonid (B)

Session Classification: Session 1 - Defect and Material Characterization